

ABSTRACT OF THE DISCLOSURE

A semiconductor device includes a trench formed on the source side of the drift region, the p-type gate region and the gate formed at the bottom of the trench, and the source formed over the entire surface of the unit device through the insulating film. The narrowest portion of the channel is deeper than one-half the junction depth of the p-type gate region. This allows the width of the channel on the drain side to be reduced even with a lower energy.